## Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

## Listing of Claims:

- (Currently Amended) A device for storing of at least one of a solid, a liquid or a gaseous object, the device having comprising:
  - at least one compartment configured to contain at least one object[[,1];
  - an electrical data memory including at least one memory cell assigned to the compartment; wherein one of placing the object in the compartment or removing the object from the compartment triggers an electrically readable signal;
  - wherein the compartment is mechanically changeable for removal of the object from the compartment or placing the object in the compartment;
  - wherein the electrically readable signal is generated after a mechanical change of the compartment;
  - wherein the memory cell adopts a memory value after the mechanical change of the compartment; and
  - wherein the compartment forms a part of the memory cell.
- 2. (Cancelled)
- (Cancelled)
- (Currently Amended) The device as claimed in claim [[27]], wherein the device further
  comprises evaluation electronics for reading the memory value from the electrical data
  memory.
- (Cancelled)

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- (Currently Amended) The device as claimed in claim [[5]]], wherein the compartment
  includes an interconnect, the interconnect being part of the memory cell, and being
  configured to be substantially destroyed after the mechanical change of the compartment.
- (Currently Amended) The device as claimed in claim [[5]], wherein the compartment forms a capacitance, the capacitance being substantially changed after the mechanical change of the compartment.
- (Currently Amended) The device as claimed in claim [[5]]1, wherein the compartment forms an inductance, the inductance being substantially changed after the mechanical change of the compartment.
- (Previously Presented) The device as claimed in claim 4, wherein the evaluation electronics comprise a shift register for reading the memory value from the electrical data memory.
- (Previously Presented) The device as claimed in claim 4, wherein the evaluation electronics comprise a terminal contact for voltage and a terminal contact for serial data transmission
- (Previously Presented) The device as claimed in claim 4, further comprising: an interface of the evaluation electronics, the interface having one or more contacts for providing data transmission; and

an external reader configured to provide data transmission through the one or more contacts of the interface.

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- (Previously Presented) The device as claimed in claim 4, wherein the evaluation electronics comprise a timer configured to generate information indicative of the time at which the compartment is mechanically changed.
- (Currently Amended) The device as claimed in claim [[6]]1, wherein at least one of [[
   one]] the memory cell, the interconnect or the evaluation electronics are integrated in a
   substrate of the device.
- (Currently Amended) The device as claimed in claim 13, wherein the electrical data memory is a write once read only memory memory integrated in the substrate.
- 15. (Previously Presented) The device as claimed in claim 13, wherein at least one of the data memory, the interconnect or the evaluation electronics are at least partly formed as polymer electronics.
- 16. (Previously Presented) The device as claimed in claim 13, wherein the device includes an assembly of layers, at least one of the layers of the assembly of layers being configured to be used for forming an electrical function.
- 17. (Previously Presented) The device as claimed in claim 16, wherein at least one of active electrical components or passive electrical components are integrated in the assembly of layers.
- (Currently Amended) The device as claimed in claim 13, wherein the substrate includes an aluminum layer the aluminium aluminum layer including the interconnect.
- (Currently Amended) The device as claimed in claim 13, wherein the substrate includes printed-on organic compounds for realization of[[t]] the interconnect.

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20. (Previously Presented) The device as claimed in claim 13, wherein the device is a pack, the pack having one or more compartments formed therein, and having the data memory and the evaluation electronics integrated in a substrate of the pack.

(Previously Presented) The device as claimed in claim 20, wherein the substrate of the
pack is configured to be a carrier for at least one of the interconnect or the evaluation
electronics.

 (Previously Presented) The device as claimed in claim 20, wherein the evaluation electronics are integrated in a chip having an integrated voltage source, the chip being attached to the pack.

(Previously Presented) The device as claimed in claim 1, wherein the device is a blister
pack.

24. (Previously Presented) The device as claimed in claim 23, wherein the blister pack includes one or more blisters, each of the one or more blisters being configured to communicate with a memory cell.

(Cancelled)

(Cancelled)

(Cancelled)

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(Previously Presented) The device as claimed in claim 4, further comprising:

 an interface of the evaluation electronics, the interface being configured to provide data transmission; and

an external reader configured to provide data transmission with the interface.

- 29. (Previously Presented) The device as claimed in claim 4, further comprising the evaluation electronics being configured to store the time at which the compartment is mechanically changed.
- 30. (Previously Presented) The device as claimed in claim 17, wherein the active electrical components includes at least one of one or more transistors or circuits formed from the one or more transistors, and wherein the passive electrical components includes at least one of one or more diodes, capacitors, inductors or resistors or circuits formed from the one or more diodes, capacitors, inductors or resistors.
- 31. (New) The device as claimed in claim 6, wherein the interconnect is integrated in a substrate of the device.